

Vishay Siliconix

Dual N-Channel 20-V MOSFET

PRODUCT SUMMARY									
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^{a, g}	Q _g (Typ.)						
20	0.216 at V _{GS} = 4.5 V	1.5							
	0.268 at V _{GS} = 2.5 V	1.5	1.2 nC						
	0.375 at V _{GS} = 1.8 V	1.0							

PowerPAK SC75-6L-Dual

FEATURES

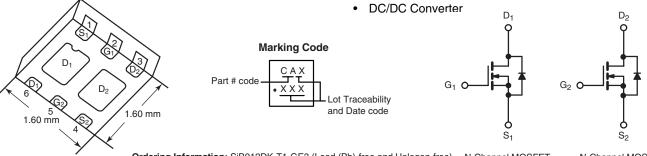
- Halogen-free
- TrenchFET[®] Power MOSFET
- New Thermally Enhanced PowerPAK[®] SC-75 Package
 - Small Footprint Area
 - Low On-Resistance



RoHS

APPLICATIONS

 Load Switch, PA Switch and Battery Switch for Portable Devices



Ordering Information: SiB912DK-T1-GE3 (Lead (Pb)-free and Halogen-free) N-Channel MOSFET

N-Channel MOSFET

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	20	V	
Gate-Source Voltage		V_{GS}	± 8		
	T _C = 25 °C		1.5 ^a		
Continuous Drain Current (T _{.1} = 150 °C)	$T_C = 70 ^{\circ}C$	I _D	1.5 ^a		
(-g)	$T_A = 25 ^{\circ}C$	٠.	1.5 ^{a, b, c}		
	T _A = 70 °C		1.4 ^{b, c}	Α	
Pulsed Drain Current		I _{DM}	5		
Continuous Source-Drain Diode Current	T _C = 25 °C	I _S	1.5 ^a		
Continuous Cource Brain Blode Current	$T_A = 25 ^{\circ}C$.5	0.9 ^{b, c}		
	T _C = 25 °C		3.1		
Maximum Power Dissipation	T _C = 70 °C	P_D	2.0	W	
Maximum Fower Dissipation	T _A = 25 °C] 'D	1.1 ^{b, c}	VV	
	T _A = 70 °C		0.7 ^{b, c}		
Operating Junction and Storage Temperature Ra	ange	T _J , T _{stg}	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature	e) ^{d, e}	· ·	260	C	

THERMAL RESISTANCE RATINGS								
Parameter		Symbol	Typical	Maximum	Unit			
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	5 s R _{thJA} 90 115 °CA		°C/W				
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	32	40	O/ V V			

Notes:

- a. Package limited.
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 5 s.
- d. See Solder Profile (http://www.vishay.com/ppg?73257). The PowerPAK SC-75 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under Steady State conditions is 125 °C/W.
- g. Based on $T_C = 25$ °C.

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SPECIFICATIONS $T_J = 25$ °C, unless otherwise noted Parameter Symbol Test Conditions Min. Typ. Max.							
Static	Syllibol	rest Conditions	IVIIII.	Тур.	IVIAX.	Unit	
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	20	<u> </u>	l	l v	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	V _G S = 0 V, I _D = 200 μ. V		22		mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA		- 2			
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	0.4	- 2	1.0		
Gate-Source Leakage	+	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$	0.4		± 100	nA	
date-source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = 10 \text{ V}$ $V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$			1	11/4	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V, T _J = 55 °C			10	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	5			Α	
On State Brain Surrent	D(OH)	V _{GS} = 4.5 V, I _D = 1.8 A		0.180	0.216		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 1.6 \text{ A}$		0.223	0.268	Ω	
Diditi-Source Off-State nesistance	' 'DS(on)	$V_{GS} = 1.8 \text{ V}, I_D = 0.3 \text{ A}$		0.223	0.200		
	0				0.375		
Forward Transconductance ^a	g _{fs}	V _{DS} = 10 V, I _D = 1.8 A		3		S	
Dynamic ^b	1 0 1				I	1	
Input Capacitance	C _{iss}			95		pF	
Output Capacitance	C _{oss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		24			
Reverse Transfer Capacitance	C _{rss}			11			
Total Gate Charge	Q_{g}	$V_{DS} = 10 \text{ V}, V_{GS} = 8 \text{ V}, I_D = 1.8 \text{ A}$		2.0	3.0	nC	
<u>-</u>				1.2	1.8		
Gate-Source Charge	Q _{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 1.8 \text{ A}$		0.3			
Gate-Drain Charge	Q_{gd}			0.15			
Gate Resistance	R_g	f = 1 MHz	0.5	2.5	5.0	Ω	
Turn-On Delay Time	t _{d(on)}			5	10		
Rise Time	t _r	$V_{DD} = 10 \text{ V}, R_L = 7.1 \Omega$		10	20	-	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 1.4 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$		24	36		
Fall Time	t _f			8	16	ns	
Turn-On Delay Time	t _{d(on)}			2	4	110	
Rise Time	t _r	V_{DD} = 10 V, R_L = 7.1 Ω		9	18	-	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 1.4 \text{ A}, V_{GEN} = 8 \text{ V}, R_g = 1 \Omega$		8	16		
Fall Time	t _f			7	14		
Drain-Source Body Diode Characterist	ics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			1.5 ^c		
Pulse Diode Forward Current	se Diode Forward Current				5	A	
Body Diode Voltage	V_{SD}	I _S = 1.4 A, V _{GS} = 0 V		0.7	1.2	٧	
Body Diode Reverse Recovery Time	t _{rr}			9	18	ns	
Body Diode Reverse Recovery Charge	Q _{rr}	1 4 4 4 41/44 400 A/ - T 05 20		3	6	nC	
Reverse Recovery Fall Time	ta	$I_F = 1.4 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$		6		ns	
Reverse Recovery Rise Time	t _b			3			

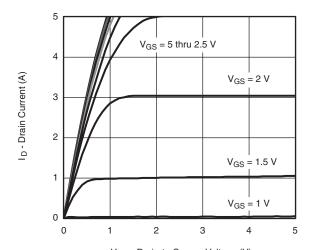
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Package limited.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



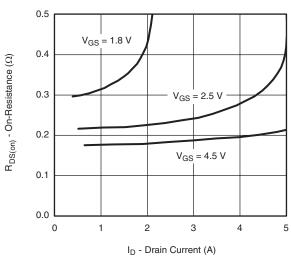
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

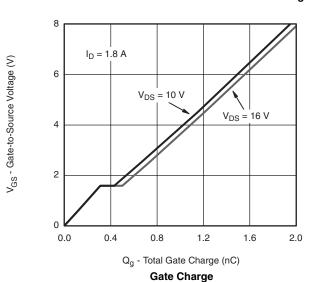


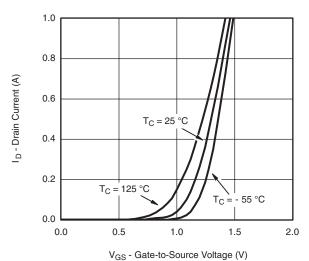
V_{DS} - Drain-to-Source Voltage (V)



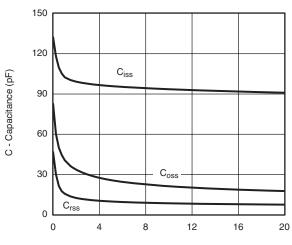


On-Resistance vs. Drain Current and Gate Voltage



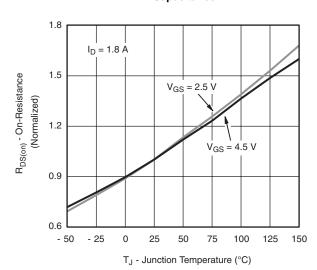


Transfer Characteristics



V_{DS} - Drain-to-Source Voltage (V)

Capacitance



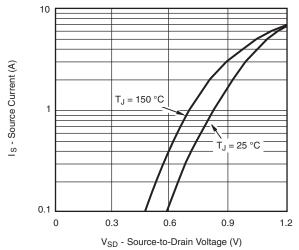
On-Resistance vs. Junction Temperature

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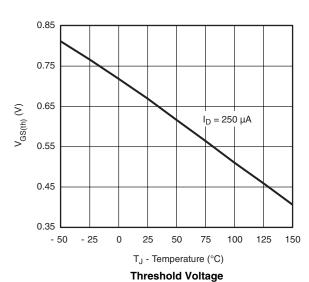
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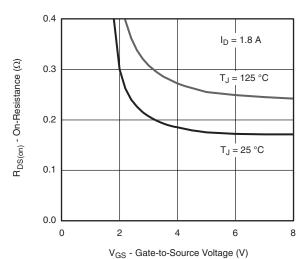
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



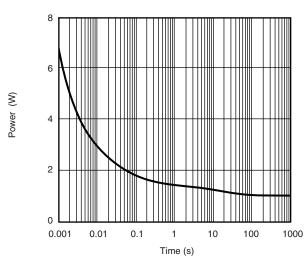
Soure-Drain Diode Forward Voltage



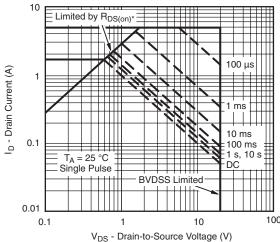
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On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient



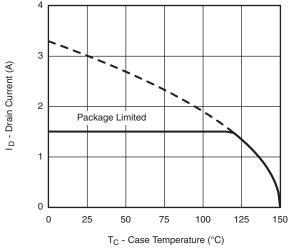
* V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified

Safe Operating Area, Junction-to-Case

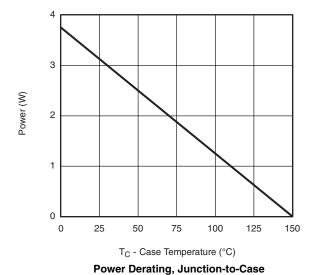


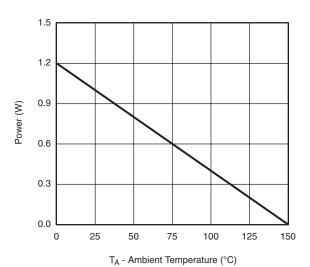
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Current Derating*





Power Derating, Junction-to-Ambient

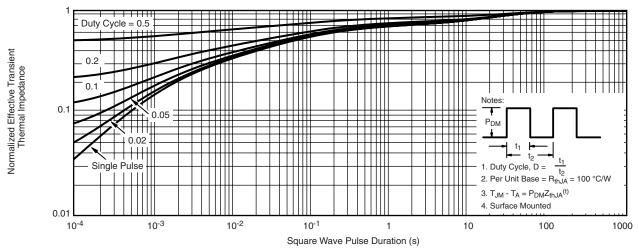
^{*} The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

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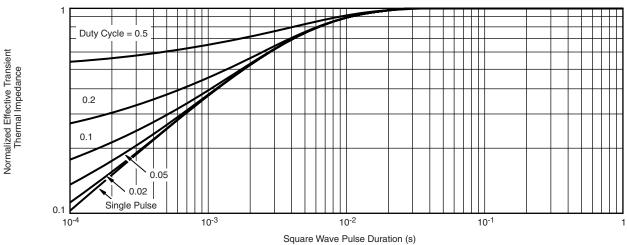
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



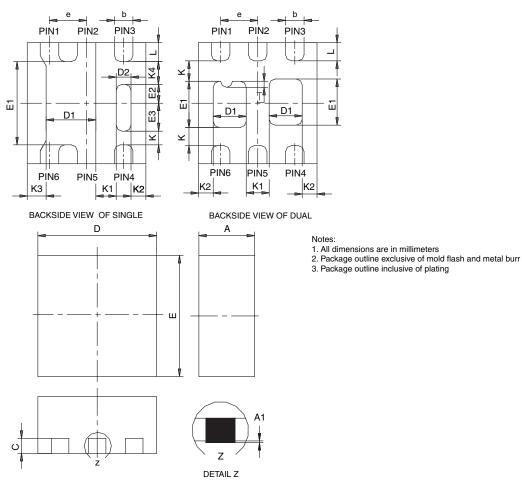
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?68883.





PowerPAK® SC75-6L



		SINGLE PAD						DUAL PAD					
DIM	MILLIMETERS			INCHES			MILLIMETERS			INCHES			
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032	
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002	
b	0.18	0.25	0.33	0.007	0.010	0.013	0.18	0.25	0.33	0.007	0.010	0.013	
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010	
D	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067	
D1	0.57	0.67	0.77	0.022	0.026	0.030	0.34	0.44	0.54	0.013	0.017	0.021	
D2	0.10	0.20	0.30	0.004	0.008	0.012							
Е	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067	
E1	1.00	1.10	1.20	0.039	0.043	0.047	0.51	0.61	0.71	0.020	0.024	0.028	
E2	0.20	0.25	0.30	0.008	0.010	0.012							
E3	0.32	0.37	0.42	0.013	0.015	0.017							
е		0.50 BSC 0.020 BSC			;	0.50 BSC			0.020 BSC				
K	0.180 TYP)		0.007 TYP		0.245 TYP				0.010 TYP		
K1	0.275 TYP				0.011 TYP		0.320 TYP 0.013 T			0.013 TYP			
K2	0.200 TYP				0.008 TYP		0.200 BSC			0.008 TYP			
K3	0.255 TYP			0.010 TYP				•					
K4	0.300 TYP			0.012 TYP									
L	0.15	0.25	0.35	0.006	0.010	0.014	0.15	0.25	0.35	0.006	0.010	0.014	
T							0.03	0.08	0.13	0.001	0.003	0.005	

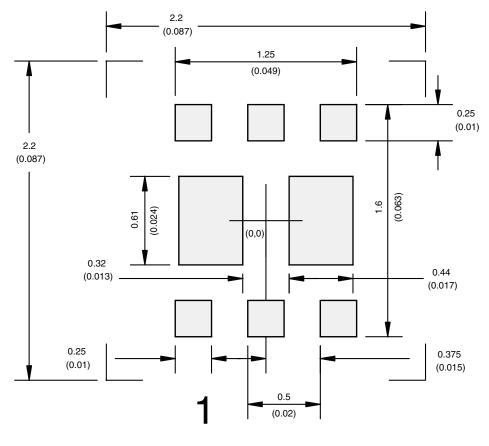
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RECOMMENDED PAD LAYOUT FOR PowerPAK® SC75-6L Dual



Dimensions in mm/(Inches)

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APPLICATION NOTE



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